

AOD607

Complementary Enhancement Mode Field Effect Transistor

General Description

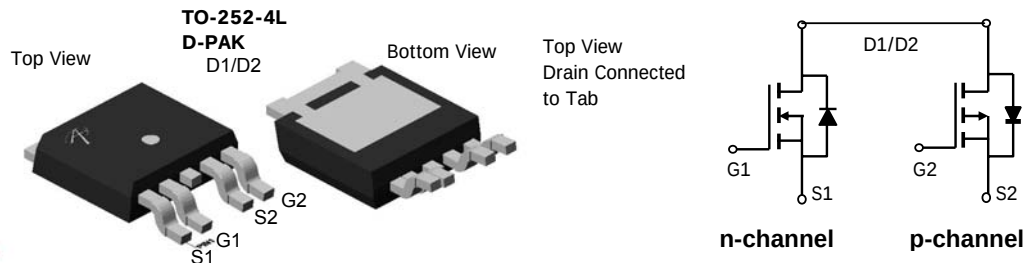
The AOD607 uses advanced trench technology MOSFETs to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used in H-bridge, Inverters and other applications.

-RoHS Compliant
-Halogen Free*

Features

n-channel	p-channel
$V_{DS} (V) = 30V$	-30V
$I_D = 12A (V_{GS}=10V)$	-12A ($V_{GS} = -10V$)
$R_{DS(ON)}$	$R_{DS(ON)}$
< 25 m Ω ($V_{GS}=10V$)	< 37 m Ω ($V_{GS} = -10V$)
< 34 m Ω ($V_{GS}=4.5V$)	< 62 m Ω ($V_{GS} = -4.5V$)

100% UIS Tested!



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current ^G	I_D	12	-12	A
$T_C=25^\circ C$		9.4	-9.4	
$T_C=100^\circ C$				
Pulsed Drain Current ^C	I_{DM}	40	-40	
Avalanche Current ^C	I_{AR}	18	-18	A
Repetitive avalanche energy $L=0.1mH$ ^C	E_{AR}	40	40	mJ
Power Dissipation ^B	P_D	25	25	W
$T_C=25^\circ C$		12.5	12.5	
$T_C=100^\circ C$				
Power Dissipation ^A	P_{DSM}	2.1	2.1	W
$T_A=25^\circ C$		1.3	1.3	
$T_A=70^\circ C$				
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	-55 to 175	$^\circ C$

Thermal Characteristics: n-channel and p-channel

Parameter	Symbol	Device	Typ	Max	
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	n-ch	19	23	$^\circ C/W$
$t \leq 10s$		n-ch	47	60	$^\circ C/W$
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	p-ch	19	23	$^\circ C/W$
Steady-State		p-ch	47	60	$^\circ C/W$
Maximum Junction-to-Case ^B	$R_{\theta JC}$	n-ch	4.5	6	$^\circ C/W$
Steady-State		p-ch	4.5	6	$^\circ C/W$

N-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.5	1.7	2.5	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	40			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =12A T _J =125°C		20 28	25 34	mΩ
		V _{GS} =4.5V, I _D =5A		27.5	34	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =12A		25		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.75	1	V
I _S	Maximum Body-Diode Continuous Current				18	A
I _{SM}	Pulsed Body-Diode Current ^C				40	A
DYNAMIC PARAMETERS						
C _{ISS}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		1040	1250	pF
C _{OSS}	Output Capacitance			180		pF
C _{rss}	Reverse Transfer Capacitance			110		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		0.7	1.5	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =12A		19.8	25	nC
Q _g (4.5V)	Total Gate Charge			9.8	12.5	nC
Q _{gs}	Gate Source Charge			2.5		nC
Q _{gd}	Gate Drain Charge			3.5		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =1.25Ω, R _{GEN} =3Ω		4.5		ns
t _r	Turn-On Rise Time			3.9		ns
t _{D(off)}	Turn-Off DelayTime			17.4		ns
t _f	Turn-Off Fall Time			3.2		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =12A, dI/dt=100A/μs		19	25	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =12A, dI/dt=100A/μs		8		nC

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B: The power dissipation P_D is based on T_{J(MAX)}=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=175°C.

D: The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

G: The maximum current rating is limited by bond-wires.

*This device is guaranteed green after data code 8X11 (Sep 1ST 2008).

Rev3: Oct 2008

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N-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

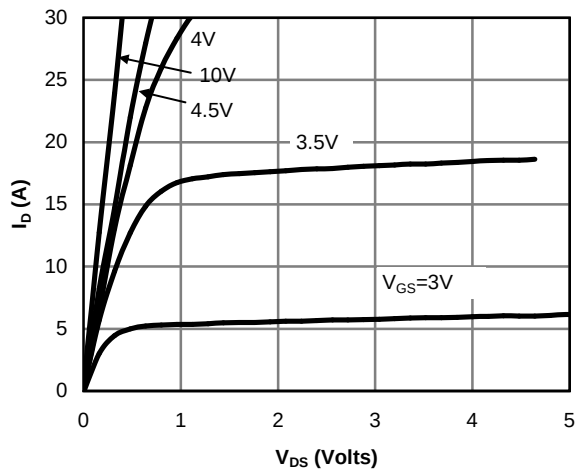


Fig 1: On-Region Characteristics

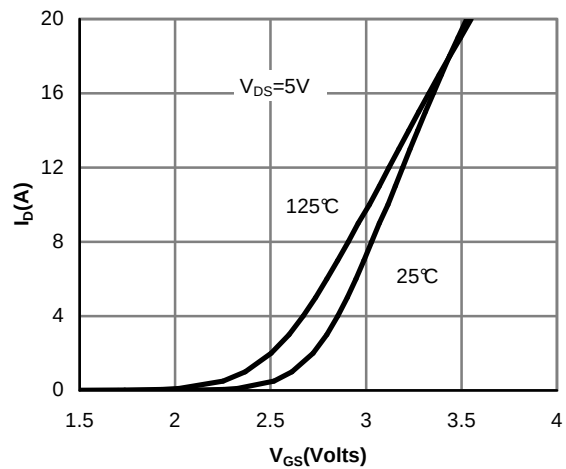


Figure 2: Transfer Characteristics

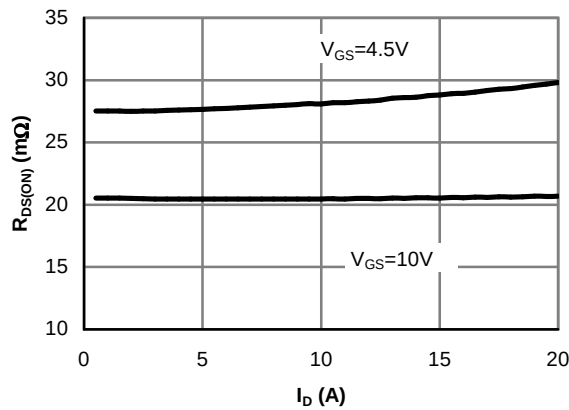


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

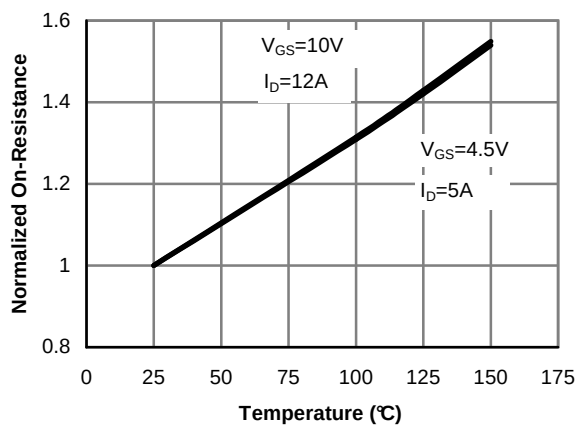


Figure 4: On-Resistance vs. Junction Temperature

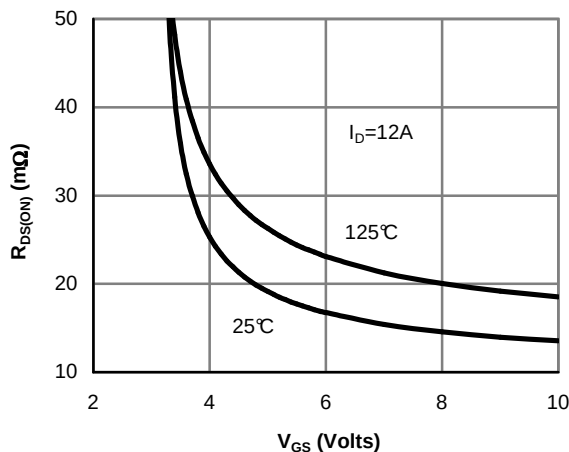


Figure 5: On-Resistance vs. Gate-Source Voltage

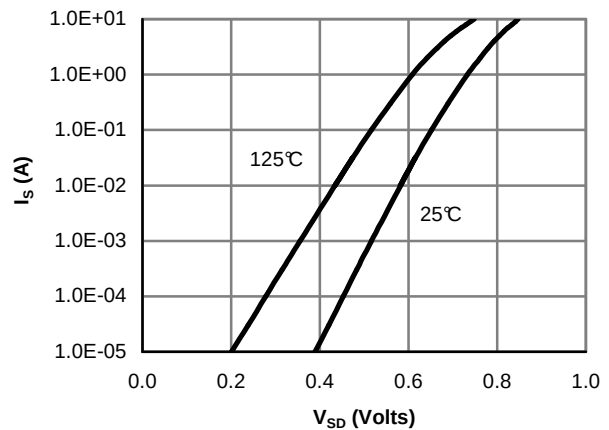


Figure 6: Body-Diode Characteristics

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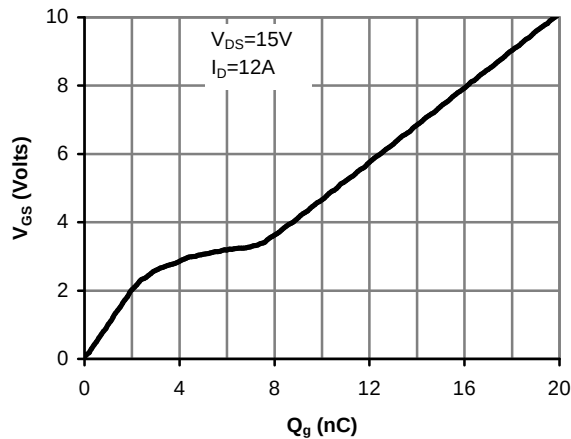


Figure 7: Gate-Charge Characteristics

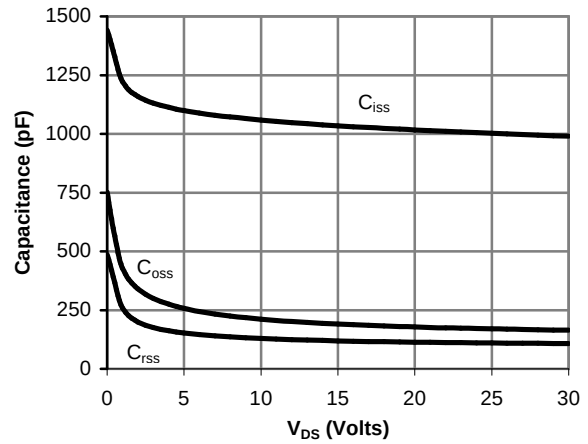


Figure 8: Capacitance Characteristics

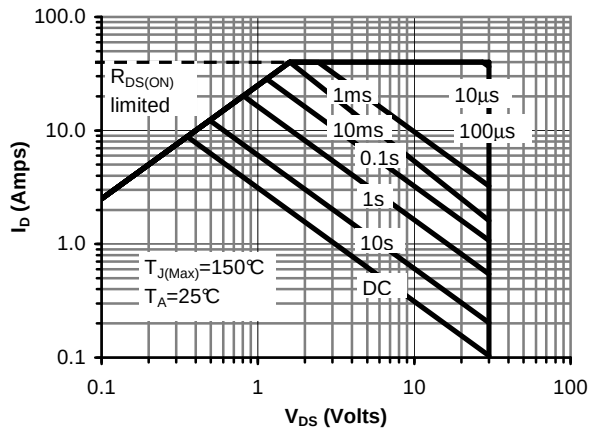


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

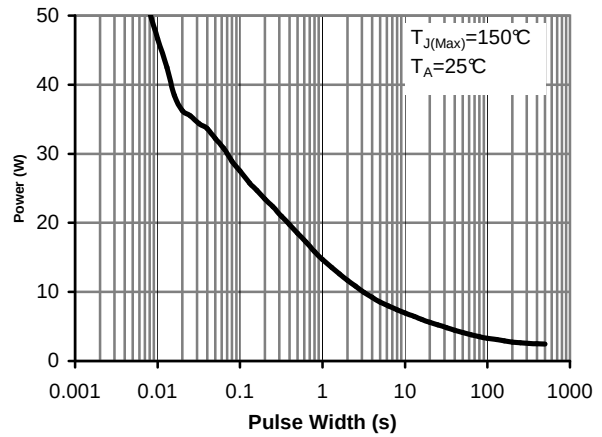


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

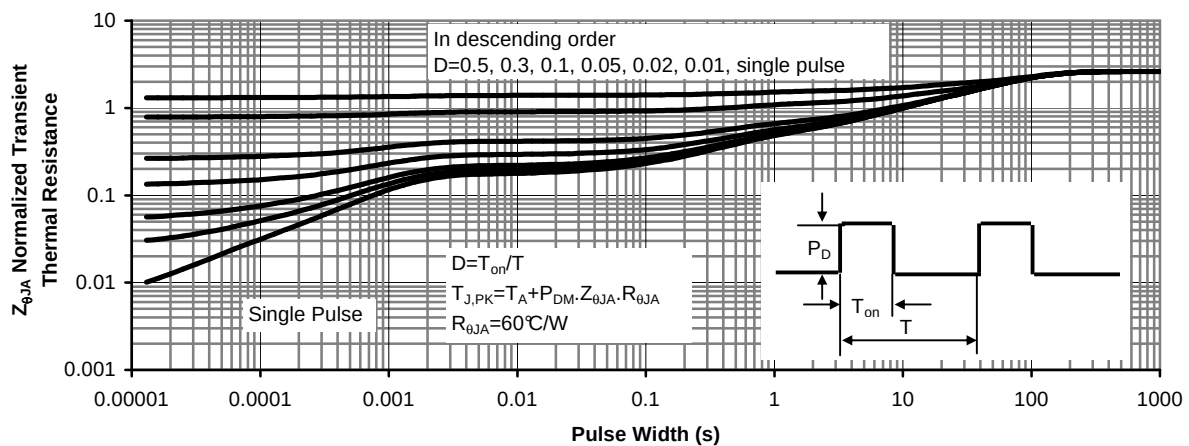


Figure 11: Normalized Maximum Transient Thermal Impedance

P-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-24V, V _{GS} =0V T _J =55°C		-0.003	-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =-250μA	-1.5	-2	-2.4	V
I _{D(ON)}	On state drain current	V _{GS} =-10V, V _{DS} =-5V	-40			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-12A T _J =125°C		30 42	37 50	mΩ
		V _{GS} =-4.5V, I _D =-5A		50	62	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-12A		17		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.76	-1	V
I _S	Maximum Body-Diode Continuous Current				-18	A
I _{SM}	Pulsed Body-Diode Current ^C				-40	A
DYNAMIC PARAMETERS						
C _{ISS}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, f=1MHz		920	1100	pF
C _{OSS}	Output Capacitance			190		pF
C _{rss}	Reverse Transfer Capacitance			122		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		3.6	5	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge (10V)	V _{GS} =-10V, V _{DS} =-15V, I _D =-12A		18.7	23	nC
Q _g (4.5V)	Total Gate Charge (4.5V)			9.7	11.7	nC
Q _{gs}	Gate Source Charge			2.54		nC
Q _{gd}	Gate Drain Charge			5.4		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-10V, V _{DS} =-15V, R _L =1.25Ω, R _{GEN} =3Ω		9	13	ns
t _r	Turn-On Rise Time			25	35	ns
t _{D(off)}	Turn-Off DelayTime			20	30	ns
t _f	Turn-Off Fall Time			12	18	ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-12A, dI/dt=100A/μs		21.4	26	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-12A, dI/dt=100A/μs		13	16	nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on steady-state R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature fo 175°C may be u sed if the PCB or heatsink allows it.

B. The power dissipation P_D is based on T_{J(MAX)}=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

C: Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=175°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

G. The maximum current rating is limited by the package current capability.

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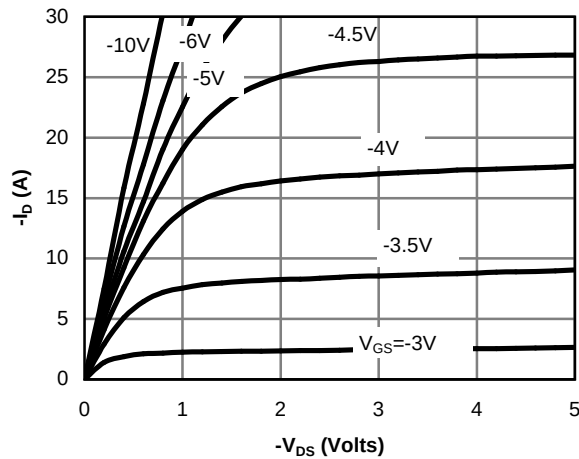


Fig 1: On-Region Characteristics

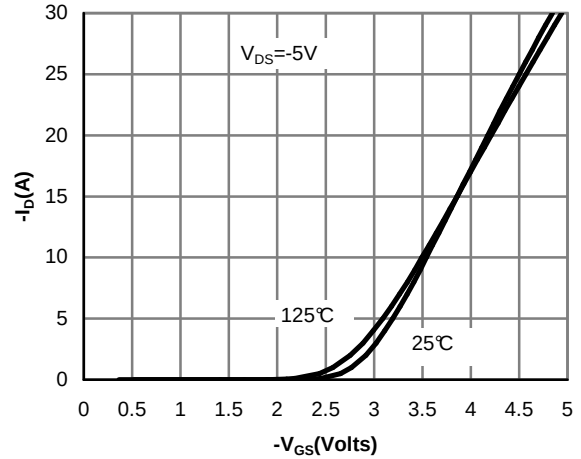


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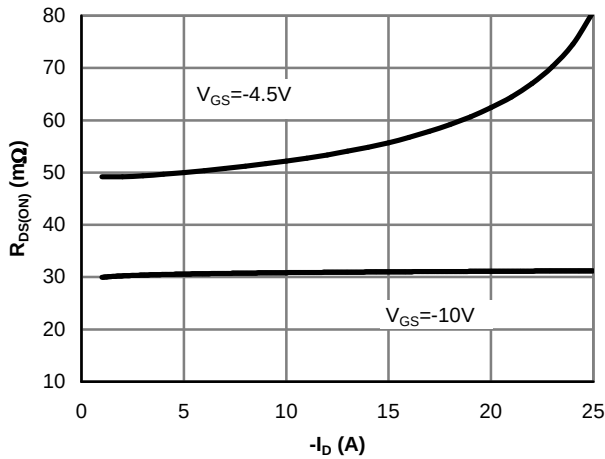


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

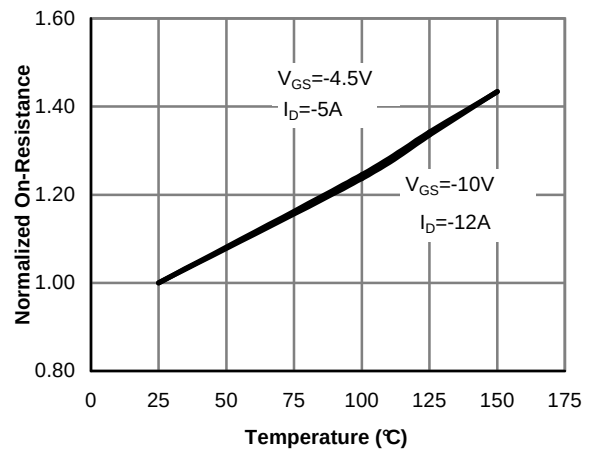


Figure 4: On-Resistance vs. Junction Temperature

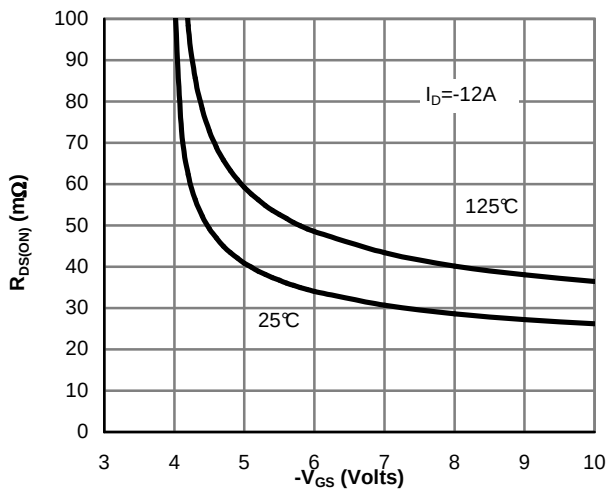


Figure 5: On-Resistance vs. Gate-Source Voltage

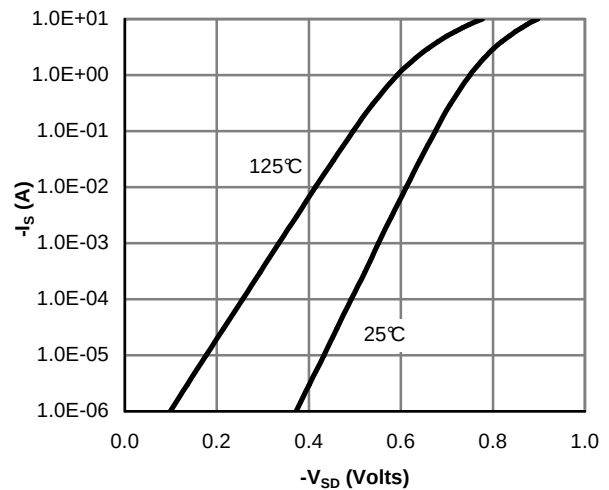


Figure 6: Body-Diode Characteristics

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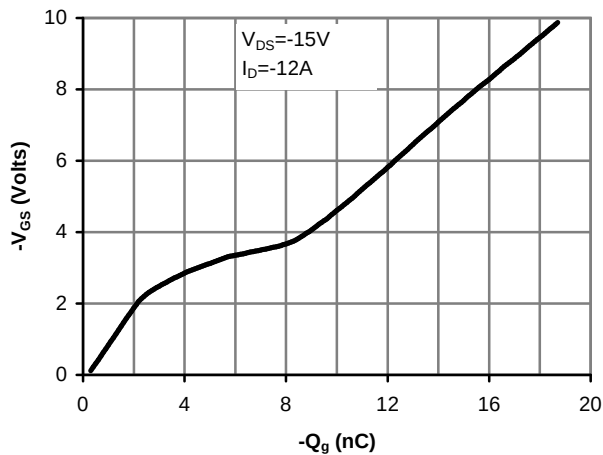


Figure 7: Gate-Charge Characteristics

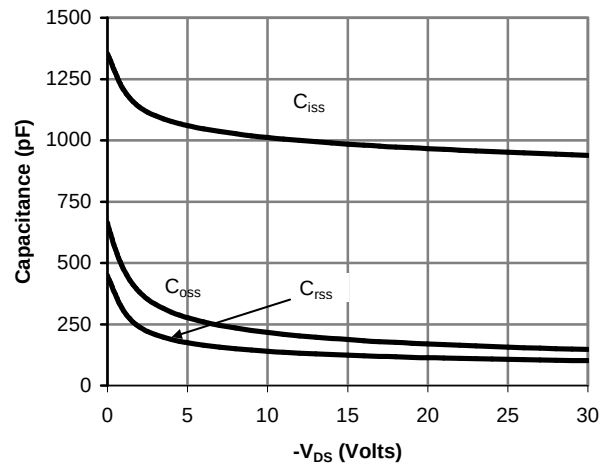


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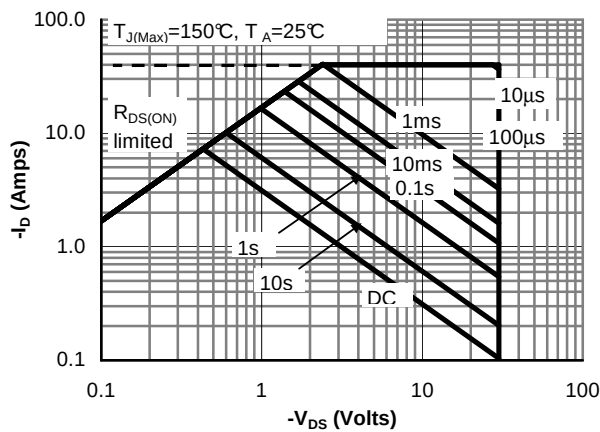


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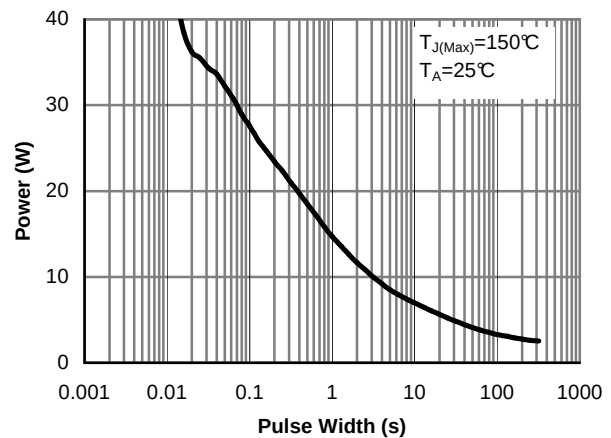


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

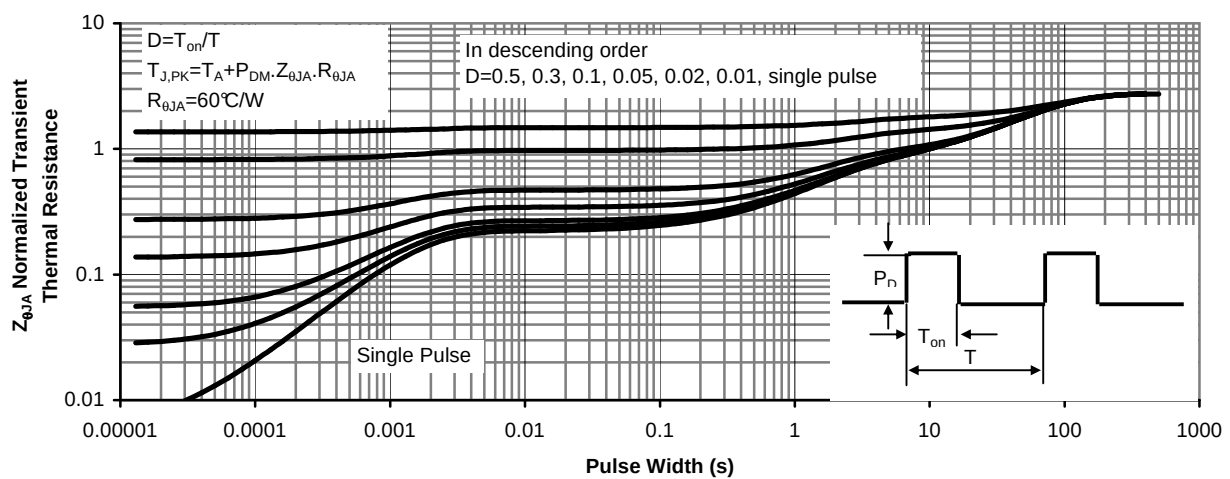
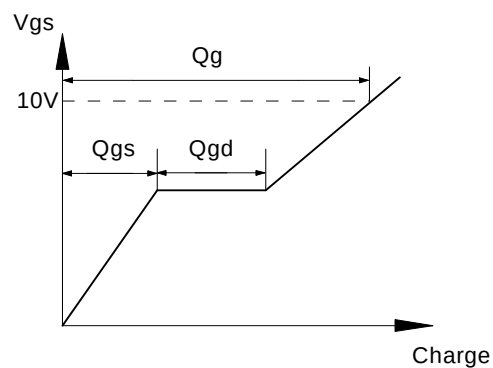
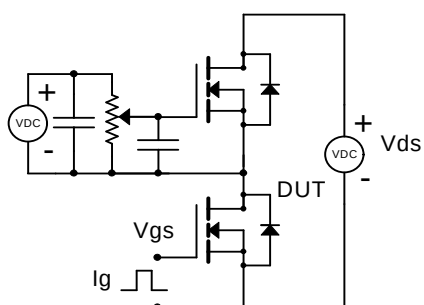
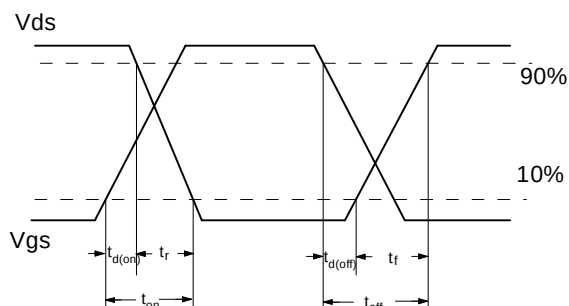
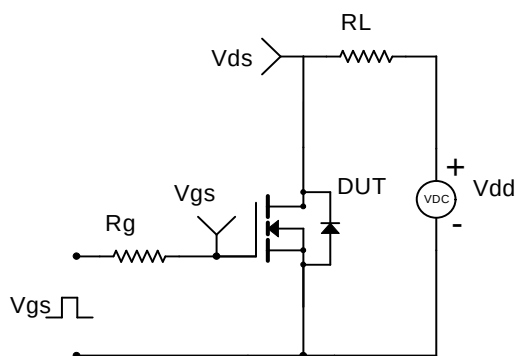


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

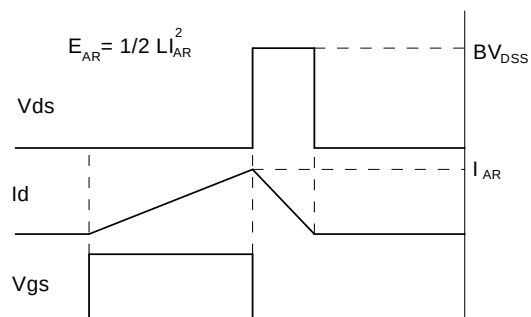
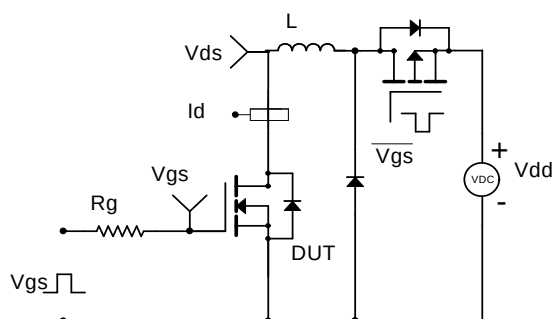
Gate Charge Test Circuit & Waveform



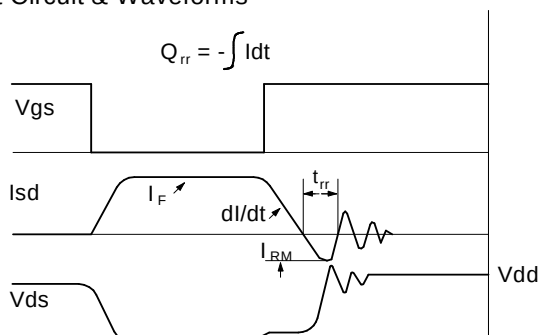
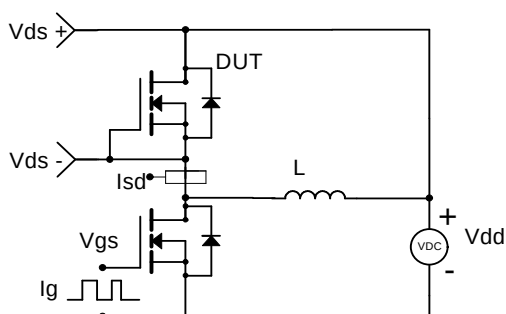
Resistive Switching Test Circuit & Waveforms



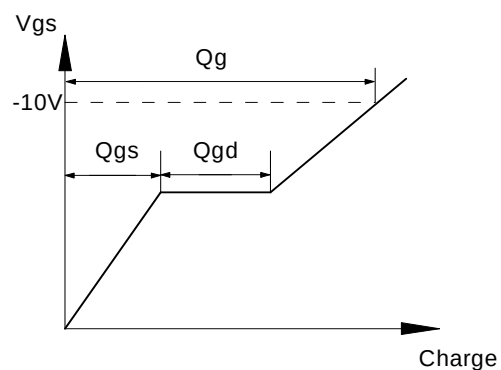
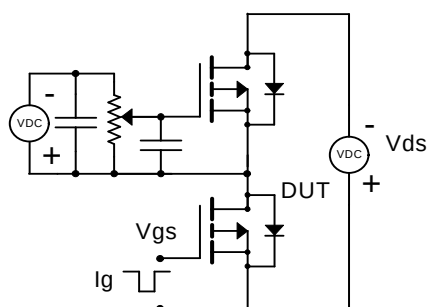
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



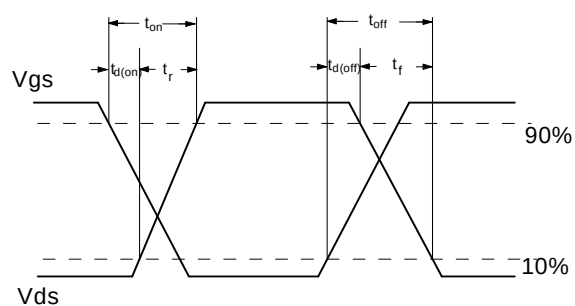
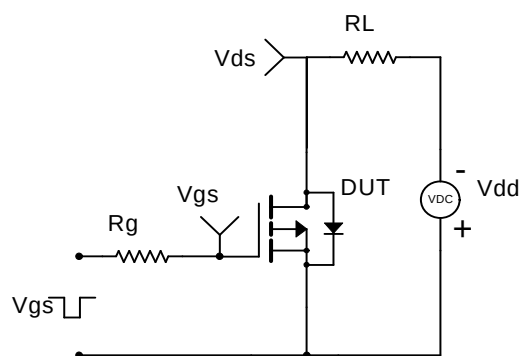
Diode Recovery Test Circuit & Waveforms



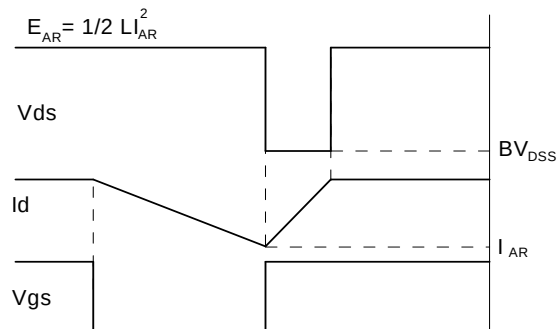
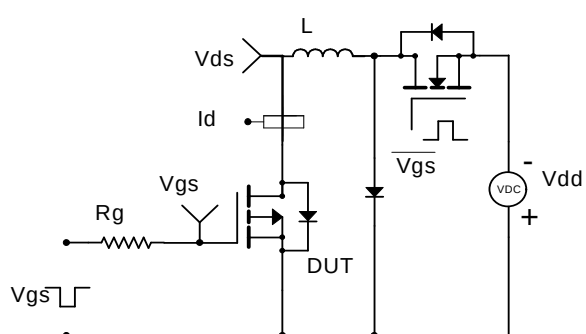
Gate Charge Test Circuit & Waveform



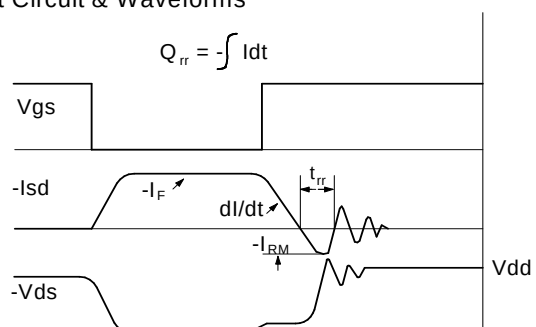
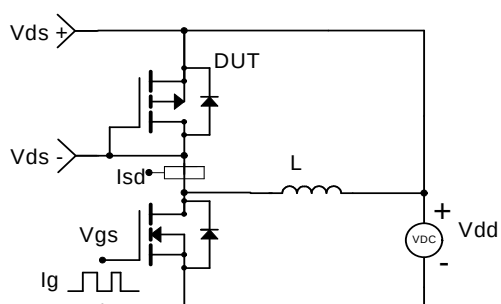
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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